

**Amendments to the Specification:**

1. Please amend the title to read:

--A METHOD OF OPERATING A SEMICONDUCTOR MEMORY ARRAY  
OF FLOATING GATE MEMORY CELLS WITH HORIZONTALLY  
ORIENTED EDGES--.

2. Please replace the first paragraph of the specification on page 1 with the following amended paragraph:

This application is a divisional application of U.S. Application No. 10/183,834, filed June 25, 2002, which claims the benefit of U.S. Provisional Application No. 60/343,634, filed December 27, 2001, [and entitled A Super Self Aligned Flash E2PROM With Vertical Word Line Transistor For Program and Horizontal Oriented Floating Gate Tips For Erase,] and of U.S. Provisional Application No. 60/355,363, filed February 6, 2002, [and entitled A Super Self Aligned Flash E2PROM With Vertical Word Line Transistor For Program and Horizontal Oriented Floating Gate Tips For Erase - SAC Option and Metal Source Line Option].